

Form PTO-1449 U.S. DEPARTMENT OF COMMERCE (REV. 8-83) PATENT AND TRADEMARK OFFICE				ATTY. DOCKET NO. BU9-98-179 US2		SERIAL NO.		
INFORMATION DISCLOSURE CITATION (Use several sheets if necessary)				APPLICANT Furukawa et al.				
				FILING DATE		GROUP		
U. S. PATENT DOCUMENTS								
EXAMINE R INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUB- CLASS	FILING DATE IF APPROPRIATE	
<i>hy</i>		5,668,065	09/1997	Lin				
		5,620,912	04/1997	Hwang et al.				
		5,397,722	03/1995	Bashir et al.				
		5,376,578	12/1994	Hsu et al.				
		5,364,804	11/1994	Ho et al.				
		5,348,900	09/1994	Ayukawa et al.				
		4,672,169	06/1987	Chambers				
<i>hy</i>		4,592,933	06/1986	Meyerson et al.				
FOREIGN PATENT DOCUMENTS								
	REF	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUB- CLASS	TRANSLATION	
							YES	NO
OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)								
<i>hy</i>		Jasinski et al. 27341 "Photochemical Deposition of Graded Silicon Nitride", Research Disclosure, January 1987, Number 273						
		Jasinski et al. 27343 "Photochemical Deposition of Silicon Nitride", Research Disclosure, January 1987, Number 273						
<i>hy</i>		Mihailescu et al. "Direct nitridation of a silicon surface by multipulse excimer laser irradiation in a nitrogen-containing ambient gas", Journal of Applied Physics <u>70</u> , August 15, 1991, pp 2123-2131.						
<i>m</i>		Mihailescu et al. "Synthesis and deposition of silicon nitride films by laser reactive ablation of silicon in low pressure ammonia: A parametric study", Journal of Vacuum Science Technology <u>14</u> , July/August 1996, pp 1986-1994.						
EXAMINER <i>Qua Hoang</i>					DATE CONSIDERED <i>7/2004</i>			
*EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.								

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<div style="text-align:center;">INFORMATION DISCLOSURE CITATION</div> <div style="text-align:left; margin-top:10px;">(Use several sheets if necessary)</div>						ATTY. DOCKET NO. BU9-98-179 US2			SERIAL NO.		
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M			Stanoslovich, et al. "Method for Reducing the Diffusion Contact Borders", IBM Technical Disclosure Bulletin, Vol. 32, No. 4A, September 1989, pgs. 344-345.								
m			Weiner et al. "Self Aligned Silicide Formation Using Gas Immersion Laser Annealing (GILA)", Ultratech Stepper technical brief, March 3, 1997.								
M			Weiner et al. "Ultrashallow Junction Formation Using Projection Gas Immersion laser Doping (PGILD)", Verdant Technologies technical brief, August 20, 1997.								
M			Derwent World Patent Index "Japanese Patent 8148680 Abstract", June 7, 1996.								
EXAMINER Quang Hoang						DATE CONSIDERED 7/2004					
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